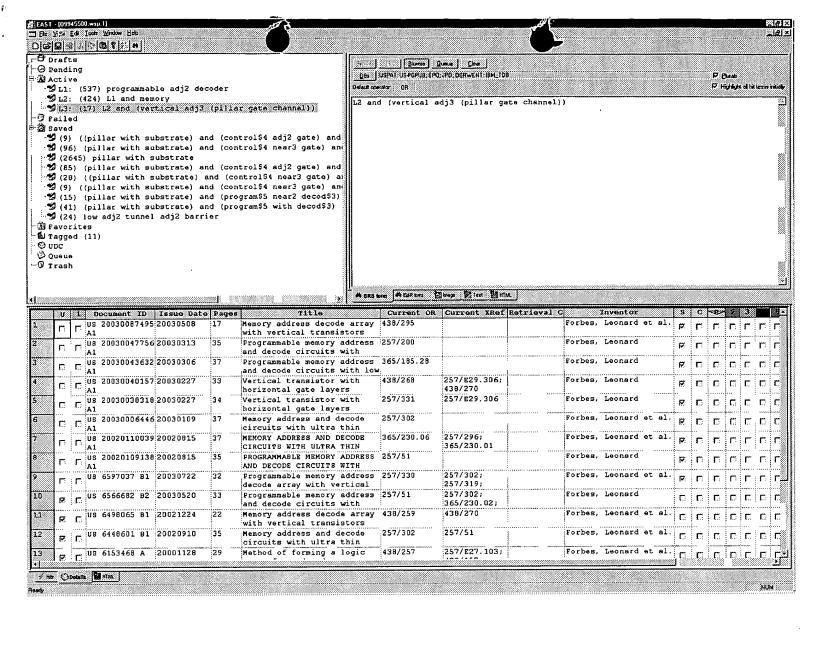


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1	г	r us	6475857	81	20021105		Method of making a scalable two transistor memory device		438/258		Kim, Woosik et al.	þ.	٣	r	r	٣	۳	r '
2	P	1 1 1	5617351				Three-dimensional direct-write EEPROM arrays	365/185.05	257/298; 257/302;		Bertin, Claude L. et al.	r	r	r	г	۳	r	r '
3	P	□ US	5455792	A	19951003		Plash EEPROM devices employing mid channel	365/185.15	257/316; 257/319;	: {	Yi, Yong-Wan	r	ព	г	г	<b>r</b> .	Б.	ר י
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Number				
1	537	programmable adj2 decoder	USPAT;	2003/12/11
			US-PGPUB;	13:56
			EPO; JPO;	
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			IBM TDB	
2	424	(programmable adj2 decoder) and memory	USPAT;	2003/12/11
			US-PGPUB;	13:56
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	17	((programmable adj2 decoder) and memory)	USPAT;	2003/12/11
		and (vertical adj3 (pillar gate channel))	US-PGPUB;	13:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	